**ORDER DESCRIPTION**

1. **Object of the contract**

The subject of the contract is a resists for nanoimprint lithography

1. **Parameters**

**2.1 Detailed scope of the subject**

| Product name | Parameter | Specification |
| --- | --- | --- |
| Resists for nanoimprint lithography | Resist NILfilm thickness - 100 nm | ImprintTechnology | Photo, UV-NIL (i-line) |
| Imprint temperature | ≈ Tg + 60 K(Tg = glass transition temperature) |
| Application | for small pattern imprinting in soft UV-NIL processes |
| Intensity light sources  | <40 mW cm-2 |
| Dry etch stability  | Substrates - silicon, quartz, aluminum |
| Filling sizes | 250 ml |
| Resist NILfilm thickness - 2 μm | ImprintTechnology | Photo, UV-NIL (i-line) |
| Imprint temperature | ≈ Tg + 60 K(Tg = glass transition temperature) |
| Application | for gas-permeable stamp materials in soft UV-NIL processes |
| Intensity light sources  | <40 mW cm-2 |
| Dry etch stability against | Substrates - silicon, quartz, aluminum |
| Filling sizes | 250 ml |
|  |  |
| Resist NILfilm thickness - 800 nm | ImprintTechnology | Photo, UV-NIL (i-line) |
| Imprint temperature | ≈ Tg + 60 K(Tg = glass transition temperature) |
| Application | for gas-permeable stamp materials in soft UV-NIL processes |
| Intensity light sources  | <40 mW cm-2 |
| Dry etch stability against | Substrates - silicon, quartz, aluminum |
| Filling sizes | 250 ml |
| Thinner for Photoresists | Technology | Organic solvent based thinner |
| Application | Thinner for the film and of hybrid polymers |
| Film thickness of hybrid polymers | < 0,5 µm |
| Filling sizes | 500 ml |
| Adhesion Promoter | AppliedTechnology | spin coating |
| Application | allows stripping of hard to removephotoresistsincreases adhesion |
| Adhesion Promoter | to difficult substrates like Au, Cu and Quartz |
| Filling sizes | 500 ml |